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BRIEF DESCRIPTION OF THE DRAWINGS

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[0005] Figs. 1 ^{through} 4 illustrate cross sectional views sequentially showing an example disclosed process of fabricating a transistor.

DETAILED DESCRIPTION

[0006] Referring to Fig. 1, after cleaning a semiconductor substrate 1 in which an active region is isolated from an inactive region by isolators 2, an oxide layer, which acts as a buffer insulation layer 3, is thermally grown and a nitride layer as a first insulation layer 4 is thickly deposited thereon.

[0007] A first photoresist pattern (not shown) for forming a gate region is formed on the first insulation layer 4 by a photolithography process. The first insulation layer 4 and the buffer insulation layer 3 may be sequentially etched by an anisotropic dry etching process using the first photoresist pattern as a mask. In the anisotropic dry etching process, the buffer insulation layer 3 is not entirely removed and remains with a small thickness. The first photoresist pattern is then removed. A polysilicon is deposited on sidewalls of the first insulation layer 4 and the buffer insulation layer 3 by using an in-situ doping process, thereby forming poly electrodes 5 for an LDD. As a result, the poly electrodes 5 are formed on an active region of a semiconductor